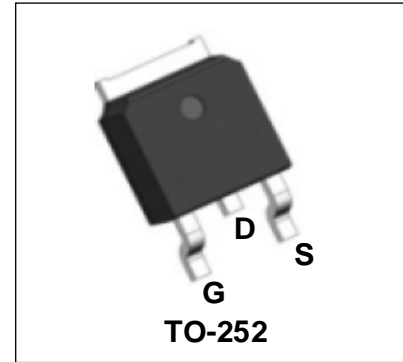


100V N-Channel Enhancement Mode Power MOSFET

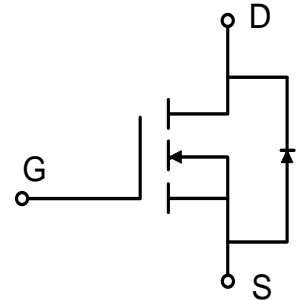
Description

WMO15N10T1 uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.



Features

- $V_{DS} = 100\text{ V}$, $I_D = 14.6\text{ A}$
 $R_{DS(on)} < 100\text{ m}\Omega$ @ $V_{GS} = 10\text{ V}$
 $R_{DS(on)} < 110\text{ m}\Omega$ @ $V_{GS} = 4.5\text{ V}$
- Green Device Available
- Low Gate Charge
- Advanced High Cell Density Trench Technology
- 100% EAS Guaranteed



Applications

- Power Management Switches
- DC/DC Converters

Absolute Maximum Ratings

Parameter		Symbol	Value	Unit
Drain-Source voltage		V_{DS}	100	V
Gate-Source voltage		V_{GS}	± 20	V
Continuous Drain Current@10V ¹	$T_C = 25^\circ\text{C}$	I_D	14.6	A
	$T_C = 100^\circ\text{C}$		10	
Pulsed Drain Current ²		I_{DM}	25	A
Single Pulse Avalanche Energy ³		EAS	3.2	mJ
Total Power Dissipation ⁴	$T_C = 25^\circ\text{C}$	P_D	30	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ¹	$R_{\theta JA}$	50	$^\circ\text{C/W}$
Thermal Resistance from Junction-to-Case ¹	$R_{\theta JC}$	3	$^\circ\text{C/W}$

Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	-	-	V
Gate-body Leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
Zero Gate Voltage Drain Current	$T_J = 25^\circ\text{C}$	I_{DSS} $V_{DS} = 80V, V_{GS} = 0V$	-	-	10	μA
	$T_J = 55^\circ\text{C}$		-	-	100	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	-	2.9	V
Drain-Source On-Resistance ²	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5A$	-	-	100	m Ω
		$V_{GS} = 4.5V, I_D = 3A$	-	-	110	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1\text{MHz}$	-	450	-	μF
Output Capacitance	C_{oss}		-	55	-	
Reverse Transfer Capacitance	C_{rss}		-	16	-	
Switching Characteristics						
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V,$ $f = 1\text{MHz}$	-	3	-	Ω
Total Gate Charge(10V)	Q_g	$V_{GS} = 10V, V_{DS} = 50V,$ $I_D = 5A$	-	11.9	-	nC
Gate-Source Charge	Q_{gs}		-	2.8	-	
Gate-Drain Charge	Q_{gd}		-	1.7	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 50V,$ $R_G = 3\Omega, I_D = 5A$	-	3.8	-	nS
Rise Time	t_r		-	25.8	-	
Turn-Off Delay Time	$t_{d(off)}$		-	16	-	
Fall Time	t_f		-	8.8	-	
Drain-source body diode Characteristics						
Diode Forward Voltage ²	V_{SD}	$I_S = 1A, V_{GS} = 0V$	-	-	1.2	V
Pulsed Source Current ^{2,5}	I_{SM}	$V_G = V_D = 0V, \text{Force Current}$	-	-	25	A
Continuous Source Current ^{1,5}	I_S		-	-	14.6	

Notes:

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- The EAS data shows Max. rating . The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.1\text{mH}, I_{AS} = 8A$
- The power dissipation is limited by 150 $^\circ\text{C}$ junction temperature
- The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

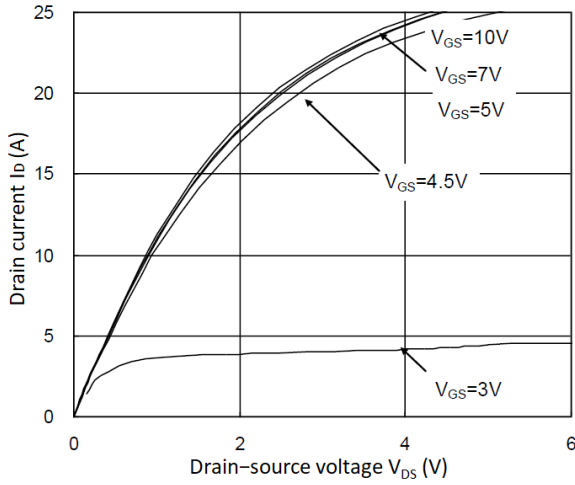


Figure 1. Output Characteristics

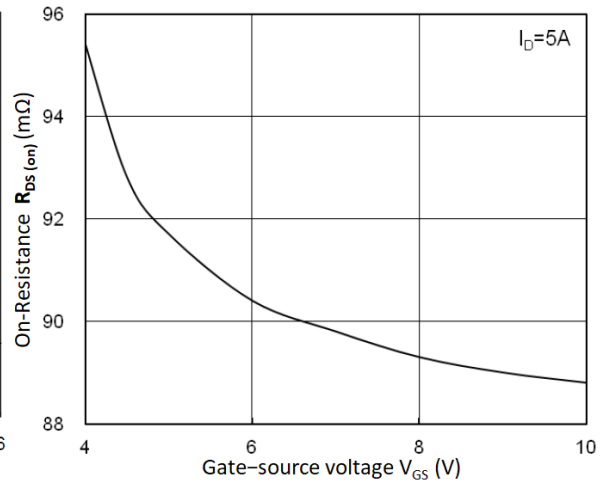


Figure 2. $R_{DS(on)}$ vs. V_{GS}

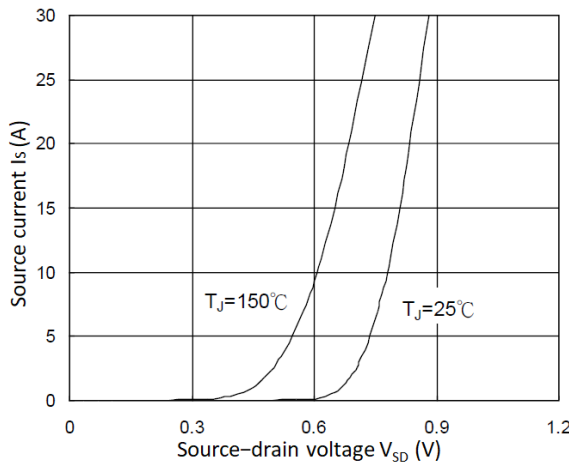


Figure 3. Forward Characteristics of Reverse

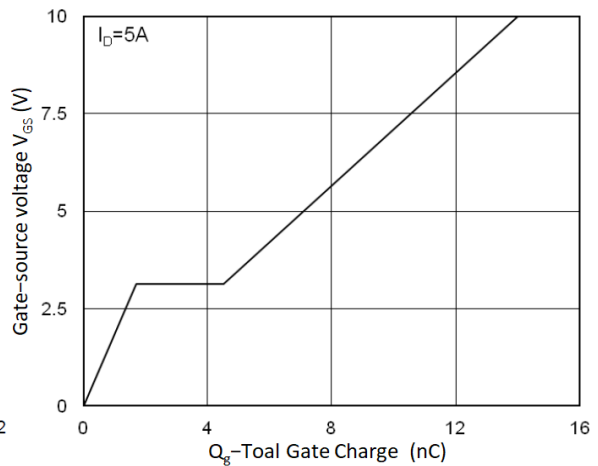


Figure 4. Gate Charge Characteristics

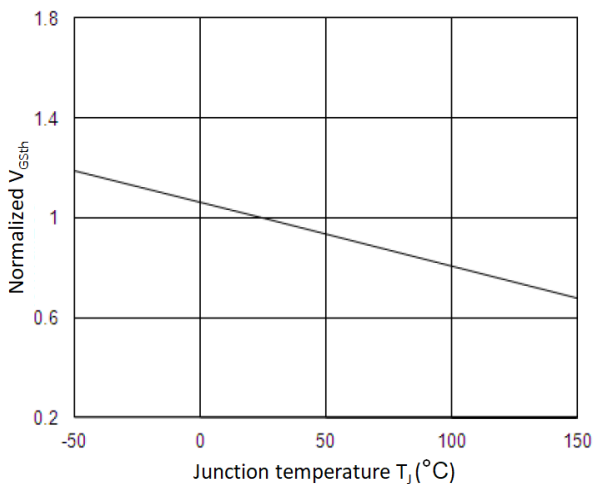


Figure 5. Normalized V_{GSth} vs. T_J

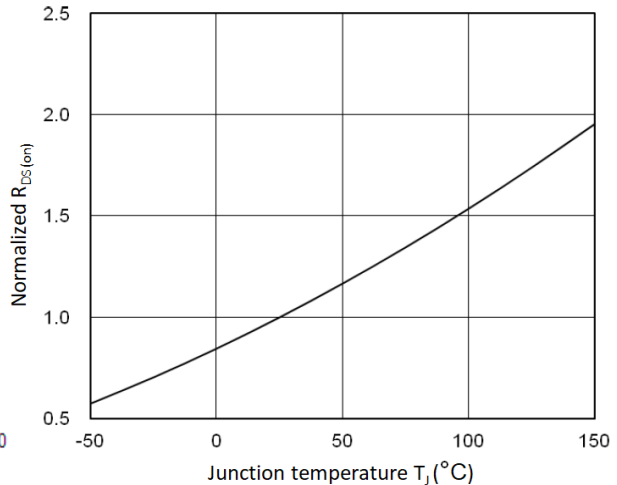


Figure 6. Normalized $R_{DS(on)}$ vs. T_J

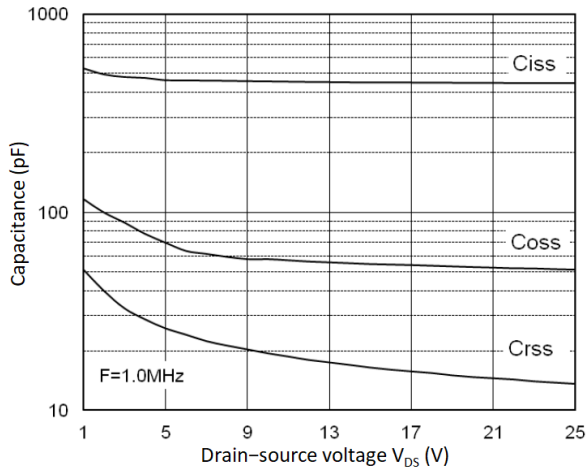


Figure 7. Capacitance Characteristics

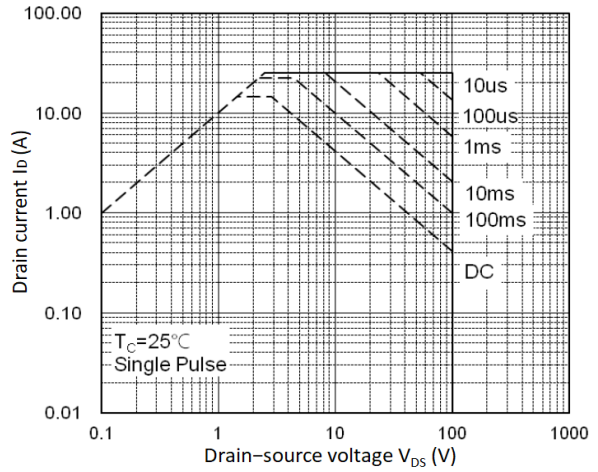


Figure 8. Safe Operating Area

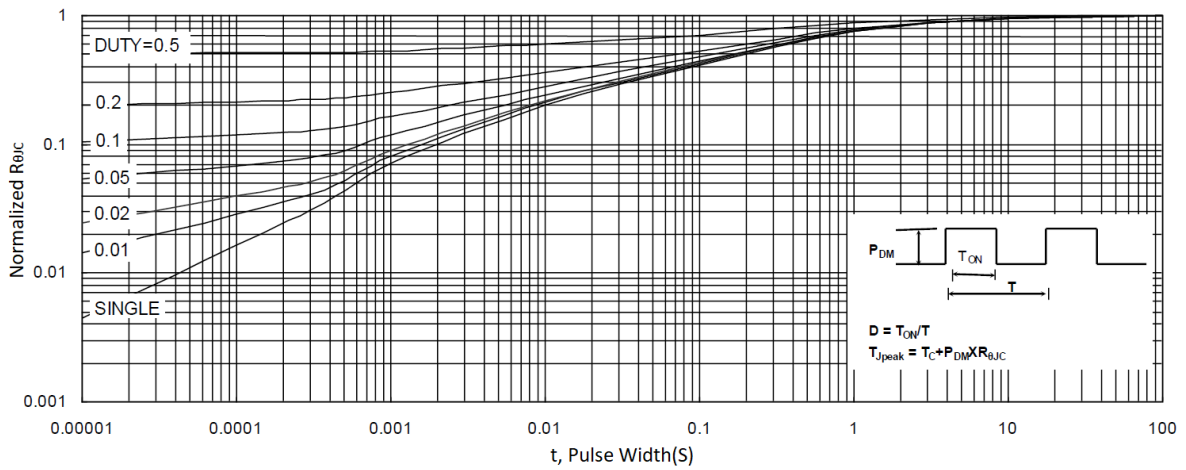


Figure 9. Normalized Maximum Transient Thermal Impedance

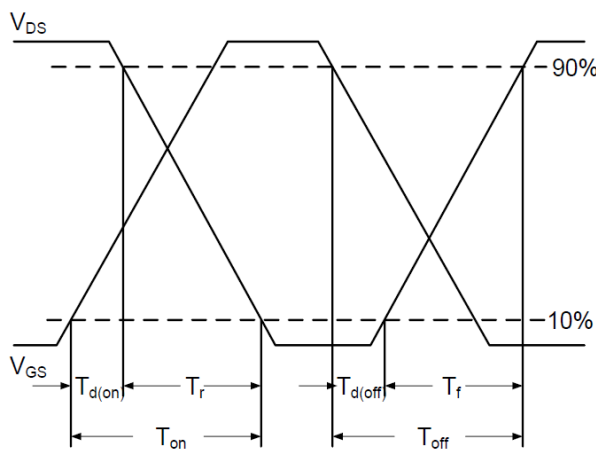


Figure 10. Switching Time Waveform

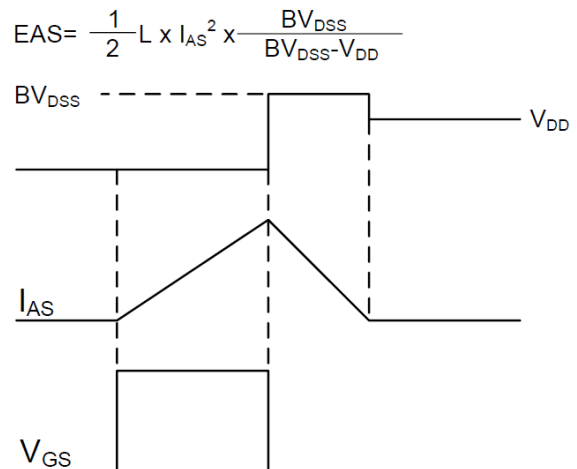
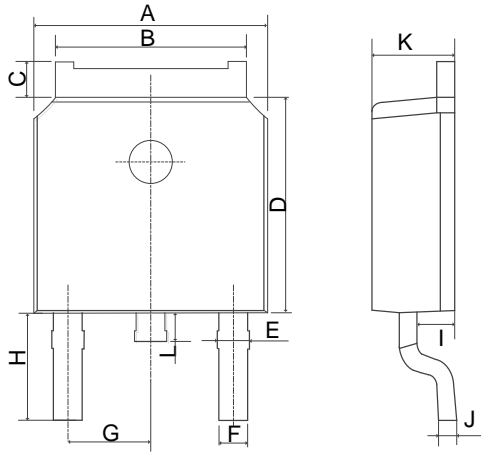


Figure 11. Unclamped Inductive Switching Waveform

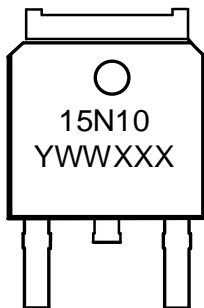
Mechanical Dimensions for TO-252

COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.50
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	2.90REF	
I	0.85	1.17
J	0.51REF	
K	2.10	2.50
L	0.40	1.00

Ordering Information

Part	Package	Marking	Packing method
WMO15N10T1	TO-252	15N10	Tape and Reel

Marking Information



15N10 = Device code

YWWXXX= Date code

Contact Information

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WAYON website: <http://www.way-on.com>

For additional information, please contact your local Sales Representative.

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